

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Specification (continued).

Please amend the ABSTRACT OF THE DISCLOSURE as set forth below.

Line 2, after "equivalent" please delete [in thickness]; same line, after "to" please insert

~~—~~ a layer of silicon dioxide having a thickness of --.

Line 3, after "or less" please delete [of silicon dioxide].

Line 5, after "source and drain" please delete [junctions] and substitute therefor –
regions --.

Line 7, after "source and drain" please delete [junctions] and substitute therefor –
regions --.

In the Claims

Please amend claim 49 as set forth below.

49. (Amended) A method for making a non-volatile semiconductor device comprising:

forming a multilayer gate dielectric having a charge storage layer [with alterable charge storage properties by application of an electric field,] and being [having a dielectric thickness] dielectrically equivalent to [that of] a layer of silicon dioxide having a thickness that is less than [about 170] 200 angstroms;

forming a gate comprising polycrystalline silicon of first conductivity type on said gate dielectric; and

forming source and drain regions separated by a channel region in a semiconductor substrate, said source and drain regions having a second conductivity type different from said first conductivity [dielectric] type.